

10/010,343

AMENDMENT IN RESPONSE TO
(OFFICE ACTION DATED FEBRUARY 27, 2003)

PATENT

AMENDMENTS TO THE SPECIFICATION

Please amend the first full paragraph on page 6 as follows:

Q, Second die 130 includes a second semiconductor substrate 132, and a micro-electromechanical block 134 that is formed on second substrate 132. Micro-electromechanical block 134, in turn, includes inductive structures, such as inductive structure 134A, that realize the functionality of a high Q inductor, and/or capacitive structures, such as capacitive structure 134B, that realize the functionality of a high Q capacitor.